## **Slotted Optical Flag Switch**

### **OPB850-1Z**





#### Features:

- Snap into PCBoard mounting
- Transistor output
- Mechanical switch replacement
- Four 18" (457 mm) 26 AWG, UL wires for electrical connections

### **Description:**

Each **OPB850-1Z** has an Rbe phototransistor coupled with an 880 nm gallium arsenide infrared emitting diode in a molded plastic housing. An actuated lever arm flag interrupts the light beam, which switches the transistor output between states that can readily drive logic gates.

These devices are designed to replace conventional mechanical limit switches where long life and reliability are critical. The switches are designed to easily snap mount into a 0.036 inch (0.914 mm) 20 gage thick material with a rectangular opening of 0.315" x 0.472 "  $(8.0 \text{ mm} \times 12.0 \text{ mm})$ .

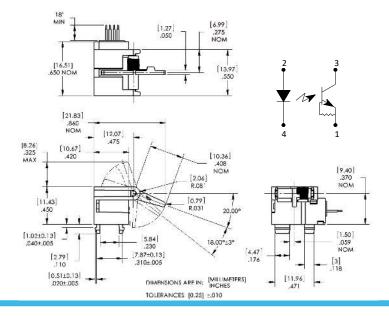
Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

### **Applications:**

- Non-contact interruptive object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety

Pin # / Color	Description	
1-Black	Emitter	
2-Red	Anode	
3-Brown	Collector	
4-Orange	Cathode	

Ordering Information						
Part Number	Wavelength	Description				
OPB850-1Z	880 nm	Slotted Optical Flag Switch 18" (457 mm) wires				



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### **Electrical Specifications**

### Absolute Maximum Ratings (T<sub>A</sub> = 25 °C unless otherwise noted)

Operating Temperature Range	-20 °C to +75 °C	
Storage Temperature Range	-40 °C to +85 °C	
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. with soldering iron]	260 °C	
Input Diode	•	
Reverse Voltage	5 V	
Continuous Forward Current	50 mA	
Peak Forward Current (10 μs pulse width, 300 pps)	1 A	
Power Dissipation	75 mW	
Output Phototransistor		
Collector-Emitter Voltage	24 V	
Emitter-Collector Voltage	5 V	
Collector DC Current	20 mA	
Power Dissipation	100 mW	

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### **Electrical Specifications**

### **Electrical Characteristics** (T<sub>A</sub> = 25 °C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
Input Diode								
$V_{F}$	Forward Voltage	-	1.2	1.6	٧	I <sub>F</sub> = 20 mA		
I <sub>R</sub>	Reverse Current	-	-	-	μΑ	V <sub>R</sub> = 2 V		
Output Phototransistor								
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	24	-	-	V	I <sub>C</sub> = 100 μA, E <sub>E</sub> = 0		
V <sub>(BR)ECO</sub>	Emitter-Collector Breakdown Voltage	0.4	-	-	V	I <sub>E</sub> = 100 μA, E <sub>E</sub> = 0		
I <sub>CEO</sub>	Collector-Emitter Dark Current	-	ı	100	nA	$V_{CE} = 10 \text{ V}, E_{E} = 0$		
Coupled								
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage (1)	-	-	0.40	٧	$I_C = 500 \mu A, I_F = 20 mA$		
I <sub>C(ON)</sub>	On-State Collector Current (1)	0.5	2	-	mA	V <sub>CE</sub> = 10 V, I <sub>F</sub> = 20 mA		
I <sub>C(OFF)</sub>	Off-State Collector Current (2)	-	-	10	μΑ	V <sub>CE</sub> = 10 V, I <sub>F</sub> = 20 mA		

#### Notes:

- (1) ON (I<sub>C(ON)</sub>) electrical condition corresponds to the switch point at about 41° angular displacement of the arm.
- (2) OFF (I<sub>C(OFF)</sub>) electrical condition corresponds to the mechanical arm position at rest.
- (3) From the rest position to the switch point, lever torque measured at the end of the arm is 1.5 grams maximum.
- (4) Wires are 26 AWG, UL rated.